



PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.2210

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Katsuhiko HIEDA et al.

Serial No.: 09/469,190

Filed: December 21, 1999

For: SEMICONDUCTOR DEVICE AND  
METHOD FOR MANUFACTURING  
THE SAME

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application as follows:

IN THE CLAIMS:

Please amend claim 18 and add new claim 24, as follows:

18. (Amended) A semiconductor device according to claim 16, wherein the capacitor insulating film is one selected from the group consisting of SrTiO<sub>3</sub>, (Ba, Sr)TiO<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub>, and Pb(Zr, Ti)O<sub>3</sub>.

Please add new claim 24, as follows:

--24. A semiconductor device according to claim 10, wherein the lower electrode is used as a memory cell of a stack-type DRAM.--

TECHNOLOGY CENTER 2800  
JUN 26 2001

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Pre  
Amend A  
LJONES  
6-27-01  
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